

## STPS30120C

#### Power Schottky rectifier

#### **Feature**

- High junction temperature capability
- Avalanche rated
- Low leakage current
- Good trade-off between leakage current and forward voltage drop

#### **Description**

Dual center tap Schottky rectifier suited for high frequency switch mode power supply.

Packaged in TO-220AB and I<sup>2</sup>PAK, this device is intended to be used in notebook and LCD adaptors, desktop SMPS, providing in these applications a margin between the remaining voltages applied on the diode and the voltage capability of the diode.

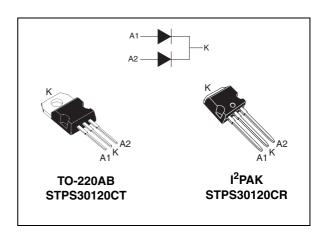


Figure 1. Electrical characteristics (a)

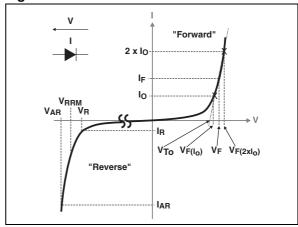


Table 1. Device summary

Symbol	Value
I <sub>F(AV)</sub>	2 x 15 A
V <sub>RRM</sub>	120 V
T <sub>j(max)</sub>	175 °C
V <sub>F(typ)</sub>	0.57 V

a.  $V_{ARM}$  and  $I_{ARM}$  must respect the reverse safe operating area defined in *Figure 11*.  $V_{AR}$  and  $I_{AR}$  are pulse measurements ( $t_p < 1~\mu s$ ).  $V_R$ ,  $I_R$ ,  $V_{RRM}$  and  $V_F$ , are static characteristics.

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### **Characteristics**

Table 2. Absolute ratings (limiting values, per diode)

Symbol	Parameter			Value	Unit
$V_{RRM}$	Repetitive peak reverse	voltage		120	V
I <sub>F(RMS)</sub>	Forward rms current			30	Α
I <sub>F(AV)</sub>	Average forward current	$\delta = 0.5$ Per diode $T_c = 145 ^{\circ}\text{C}$ Per device		15 30	Α
I <sub>FSM</sub>	Surge non repetitive forw	vard current	180	Α	
P <sub>ARM</sub>	Repetitive peak avalanch	ne power $t_p = 1 \mu s T_j = 25 °C$		6700	W
V <sub>ARM</sub> <sup>(1)</sup>	Maximum repetitive peak avalanche voltage	t <sub>p</sub> = 1 μs, T <sub>j</sub> < 150 °C, I <sub>AR</sub> < 13.4 A		150	V
V <sub>ASM</sub> <sup>(1)</sup>	Maximum single pulse peak avalanche voltage	$t_p = 1 \mu s, T_j < 15$	150	V	
T <sub>stg</sub>	Storage temperature range			-65 to + 175	°C
Tj	Maximum operating junction temperature <sup>(2)</sup>			175	°C

Table 3. Thermal parameters

Symbol	Parameter	Value	Unit	
R <sub>th(j-c)</sub>	Junction to case	Per diode Total	2.2 1.3	°C/W
R <sub>th(c)</sub>	Coupling	Total	0.3	°C/W

When the diodes 1 and 2 are used simultaneously :

 $T_j(diode 1) = P(diode 1) \times R_{th(j-c)}(per diode) + P(diode 2) \times R_{th(c)}$ 

<sup>1.</sup> Refer to Figure 11
2.  $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$  condition to avoid thermal runaway for a diode on its own heatsink

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Table 4.	Static electrical	characteristics (	(per diode)

Symbol	Test conditions			Min.	Тур.	Max.	Unit
ı_(1)	In(!)   Reverse leakage current   L	T <sub>j</sub> = 25 °C	$V_R = V_{RRM}$			15	μΑ
'R`		T <sub>j</sub> = 125 °C			2.5	7.5	mA
	V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 5 A			0.74	
		T <sub>j</sub> = 125 °C			0.57	0.61	
V (2)		T <sub>j</sub> = 25 °C				0.92	V
v <sub>F</sub> `′		T <sub>j</sub> = 125 °C	I <sub>F</sub> = 15 A		0.7	0.74	V
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 30 A			1.02	
		T <sub>j</sub> = 125 °C	1 IF = 30 A		0.83	0.89	

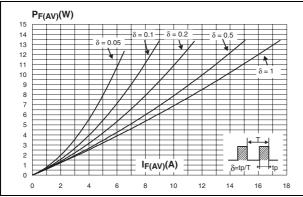
- 1. Pulse test : tp = 5 ms,  $\delta$  < 2%
- 2. Pulse test : tp = 380  $\mu$ s,  $\delta$  < 2%

To evaluate the maximum conduction losses use the following equation :

 $P = 0.59 \times I_{F(AV)} + 0.01 I_{F}^{2}(RMS)$ 

Figure 2. Average forward power dissipation versus average forward current (per diode)

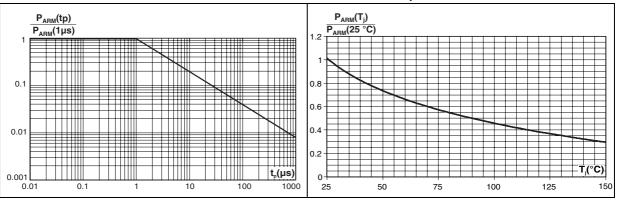
Figure 3. Average forward current versus ambient temperature ( $\delta$  = 0.5, per diode)



| F(AV)(A) | 18 | 16 | 14 | 12 | 10 | 12 | 15 | 150 | 175 | 100 | 125 | 150 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 | 175 |

Figure 4. Normalized avalanche power derating versus pulse duration

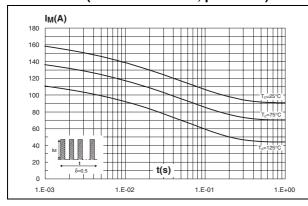
Figure 5. Normalized avalanche power derating versus junction temperature



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Figure 6. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

Figure 7. Relative variation of thermal impedance junction to ambient versus pulse duration



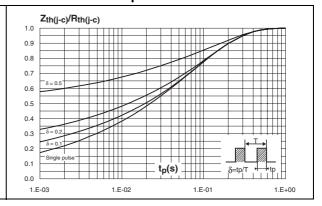
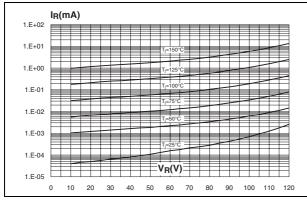


Figure 8. Reverse leakage current versus reverse voltage applied (typical values, per diode)

Figure 9. Junction capacitance versus reverse voltage applied (typical values, per diode)



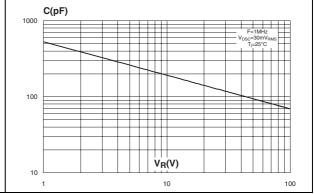
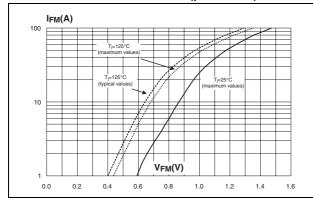
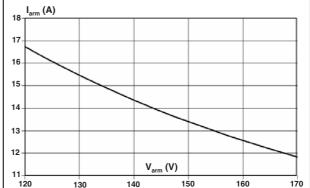


Figure 10. Forward voltage drop versus forward current (per diode)

Figure 11. Reverse safe operating area  $(t_p < 1 \ \mu s \ and \ T_j < 150 \ ^{\circ}C)$ 





### 2 Package information

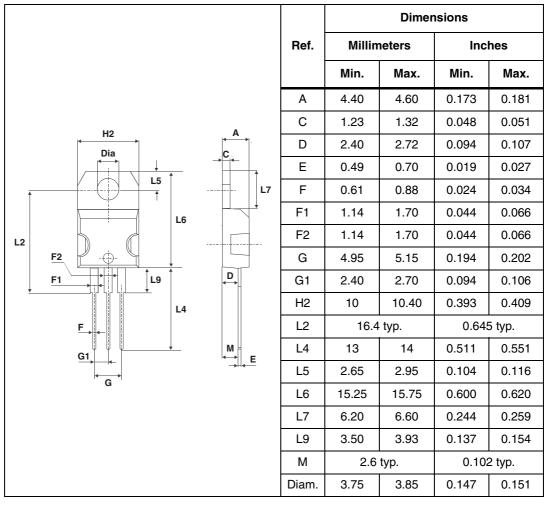
Epoxy meets UL94, V0

Cooling method: by conduction (C)

Recommended torque value: 0.4 to 0.6 N·m

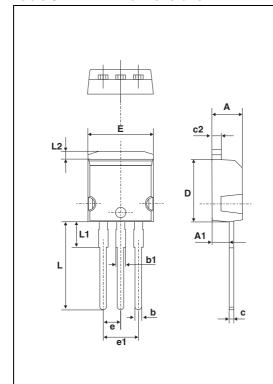
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

Table 5. TO-220AB dimensions



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Table 6. I<sup>2</sup>PAK dimensions



	Dimensions				
Ref.	. Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	4.40	4.60	0.173	0.181	
A1	2.40	2.72	0.094	0.107	
b	0.61	0.88	0.024	0.035	
b1	1.14	1.70	0.044	0.067	
С	0.49	0.70	0.019	0.028	
c2	1.23	1.32	0.048	0.052	
D	8.95	9.35	0.352	0.368	
е	2.40	2.70	0.094	0.106	
e1	4.95	5.15	0.195	0.203	
Е	10	10.40	0.394	0.409	
L	13	14	0.512	0.551	
L1	3.50	3.93	0.138	0.155	
L2	1.27	1.40	0.050	0.055	

## **3** Ordering information

 Table 7.
 Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS30120CT	STPS30120CT	TO-220AB	2.23 g	50	Tube
STPS30120CR	STPS30120CR	I <sup>2</sup> PAK	1.49 g	50	Tube

# 4 Revision history

Table 8. Document revision history

Date	Revision	Changes
18-Feb-2005	1	First issue.
23-Nov-2006	2	Reformatted to current standards. Added I <sup>2</sup> PAK package.
17-Feb-2010	3	Updated Table 2. Added Figure 1 and Figure 11.

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